

**General Description**

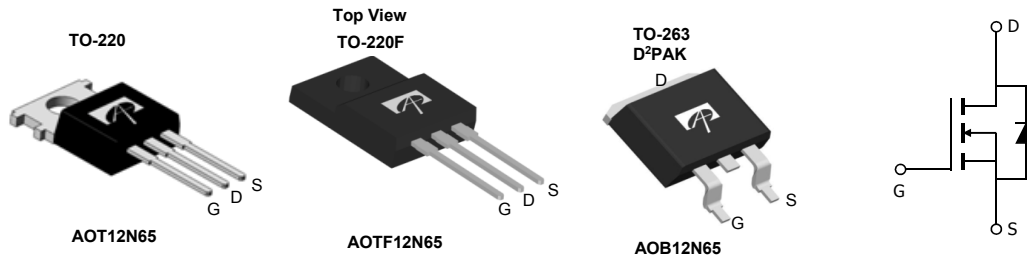
The AOT12N65 & AOTF12N65 & AOB12N65 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.

By providing low  $R_{DS(on)}$ ,  $C_{iss}$  and  $C_{rss}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

**Product Summary**

$V_{DS}$	750V@150°C
$I_D$ (at $V_{GS}=10V$ )	12A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 0.72Ω

100% UIS Tested  
 100%  $R_g$  Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT12N65	TO-220 Pb Free	Tube	1000
AOTF12N65	TO-220F Pb Free	Tube	1000
AOTF12N65L	TO-220F Green	Tube	1000
AOB12N65L	TO-263 Green	Tape & Reel	800

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOT(B)12N65	AOTF12N65	AOTF12N65L	Units	
Drain-Source Voltage	$V_{DS}$	650			V	
Gate-Source Voltage	$V_{GS}$	±30			V	
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	12	12*	A	
		$T_C=100^\circ\text{C}$	7.7	7.7*		
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	48			A	
Avalanche Current <sup>C</sup>	$I_{AR}$	5			A	
Repetitive avalanche energy <sup>C</sup>	$E_{AR}$	375			mJ	
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	750			mJ	
MOSFET dv/dt ruggedness	dv/dt	30			V/ns	
Peak diode recovery dv/dt		5				
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	278	50	40	W
		Derate above 25°C	2.2	0.4	0.3	W/°C
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150			°C	
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300			°C	

**Thermal Characteristics**

Parameter	Symbol	AOT(B)12N65	AOTF12N65	AOTF12N65L	Units
Maximum Junction-to-Ambient <sup>A,D</sup>	$R_{\theta JA}$	65	65	65	°C/W
Maximum Case-to-sink <sup>A</sup>	$R_{\theta CS}$	0.5	--	--	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.45	2.5	3.1	°C/W

\* Drain current limited by maximum junction temperature.

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	650			V
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C		750		
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		0.72		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =520V, T <sub>J</sub> =125°C			10	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V, I <sub>D</sub> =250μA	3	3.9	4.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		0.57	0.72	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =6A		17		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.71	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				12	A
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current				48	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	1430	1792	2150	pF
C <sub>oss</sub>	Output Capacitance		120	152	185	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		9	11.5	18	pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	1.7	3.5	5.3	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =520V, I <sub>D</sub> =12A	32	39.8	48	nC
Q <sub>gs</sub>	Gate Source Charge		7.5	9.2	11	nC
Q <sub>gd</sub>	Gate Drain Charge		13.5	16.8	20	nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =325V, I <sub>D</sub> =12A, R <sub>G</sub> =25Ω		36		ns
t <sub>r</sub>	Turn-On Rise Time			77		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			120		ns
t <sub>f</sub>	Turn-Off Fall Time			63		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time		I <sub>F</sub> =12A, dI/dt=100A/μs, V <sub>DS</sub> =100V	300	375	450
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =12A, dI/dt=100A/μs, V <sub>DS</sub> =100V	6	7.5	9	μC

A. The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25° C.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C, Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

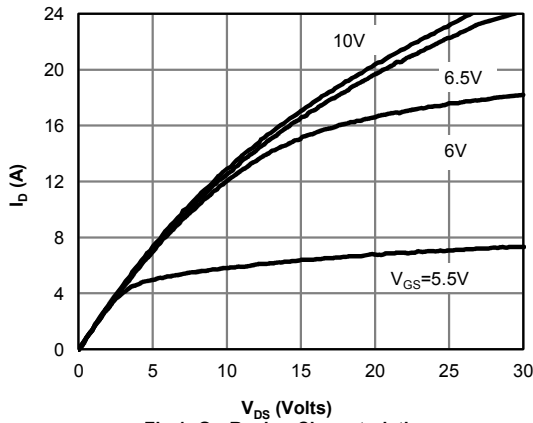
E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

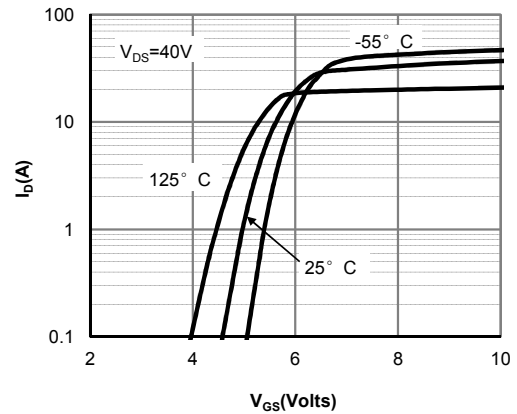
G. L=60mH, I<sub>AS</sub>=5A, V<sub>DD</sub>=150V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25° C

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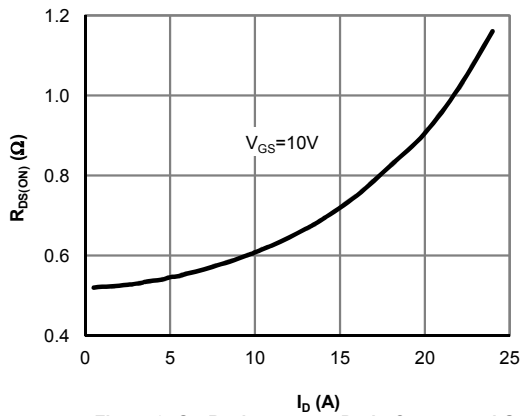
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



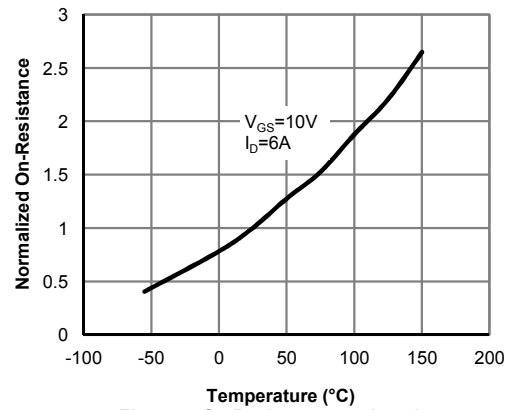
**Fig 1: On-Region Characteristics**



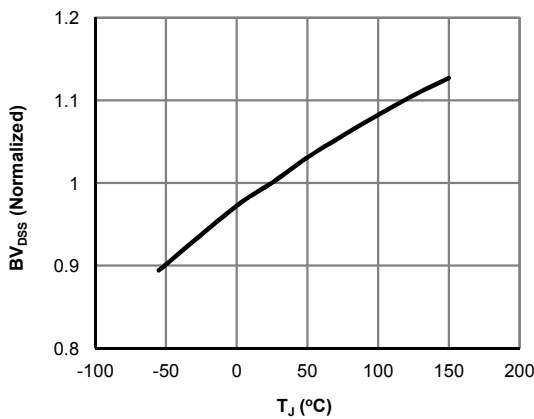
**Figure 2: Transfer Characteristics**



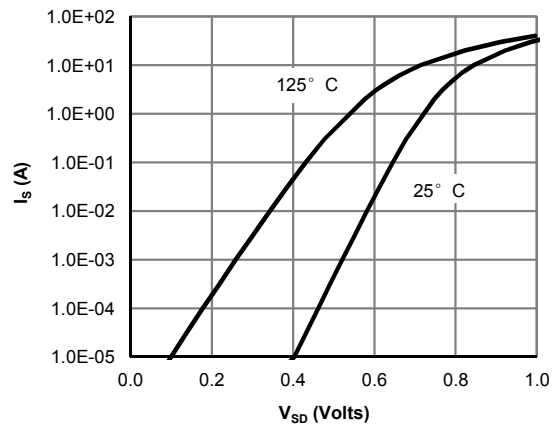
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5: Break Down vs. Junction Temperature**



**Figure 6: Body-Diode Characteristics (Note E)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

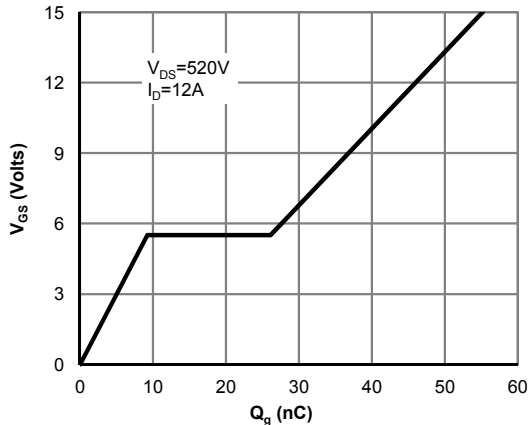


Figure 7: Gate-Charge Characteristics

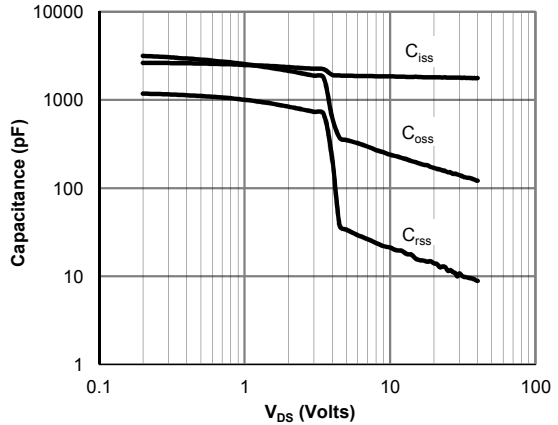


Figure 8: Capacitance Characteristics

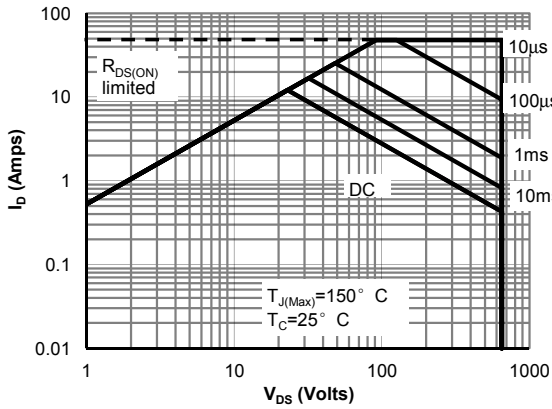


Figure 9: Maximum Forward Biased Safe Operating Area for AOT(B)12N65 (Note F)

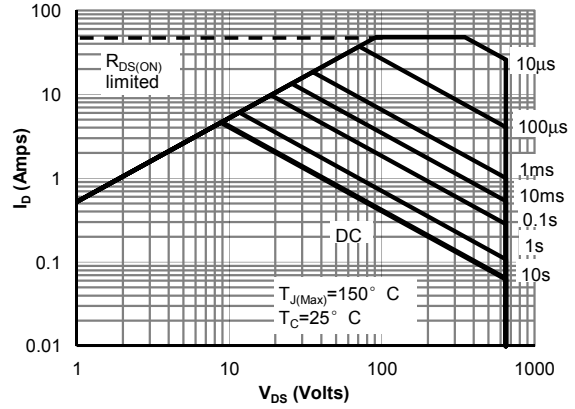


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF12N65 (Note F)

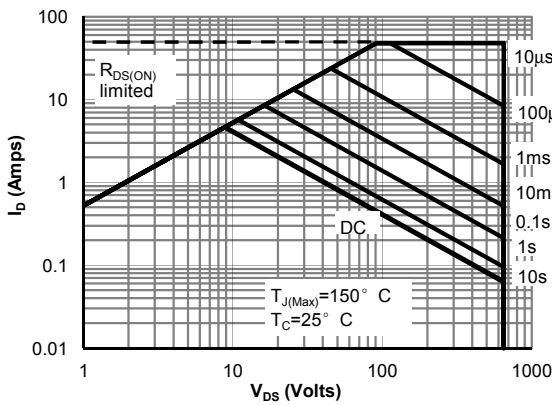


Figure 11: Maximum Forward Biased Safe Operating Area for AOTF12N65L (Note F)

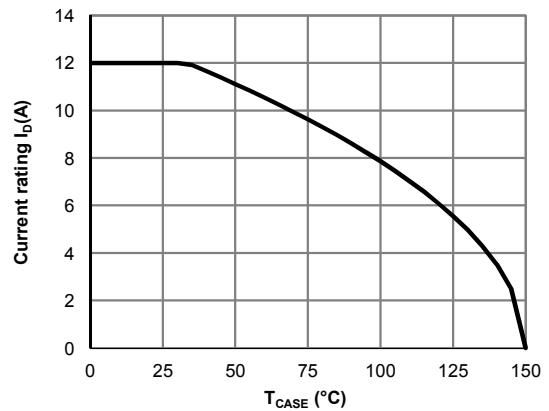
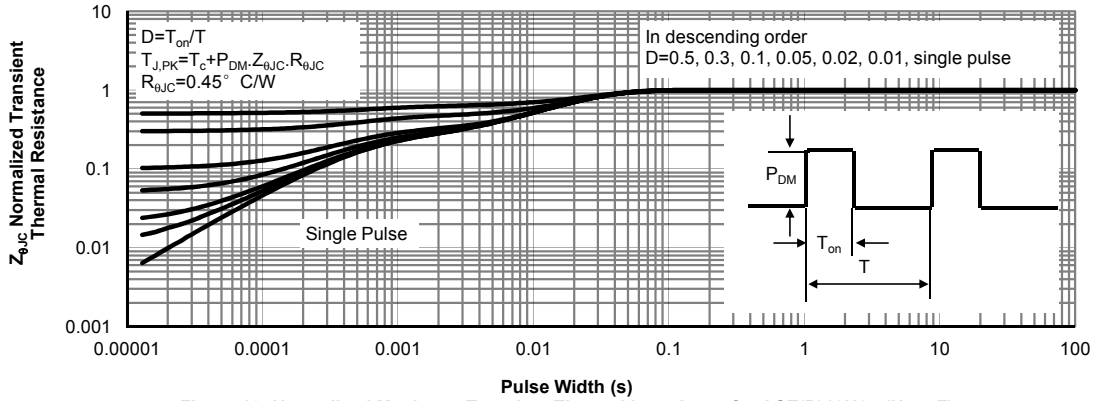
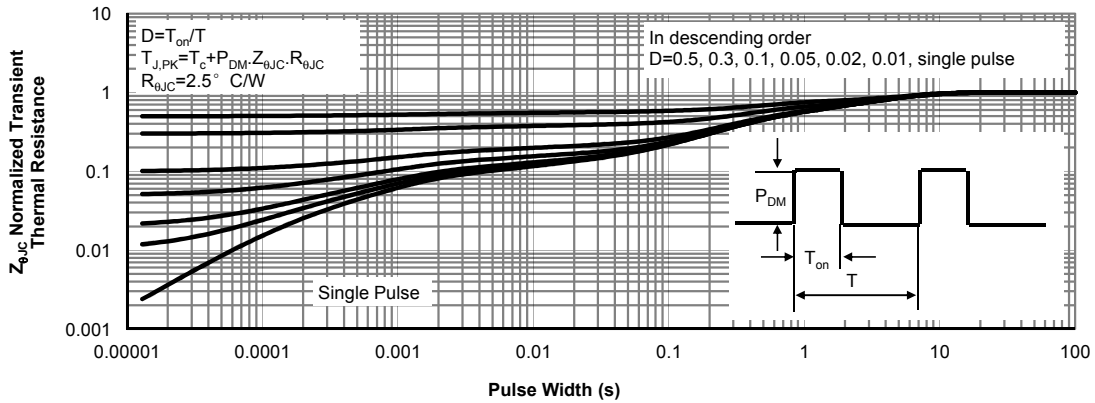


Figure 12: Current De-rating (Note B)

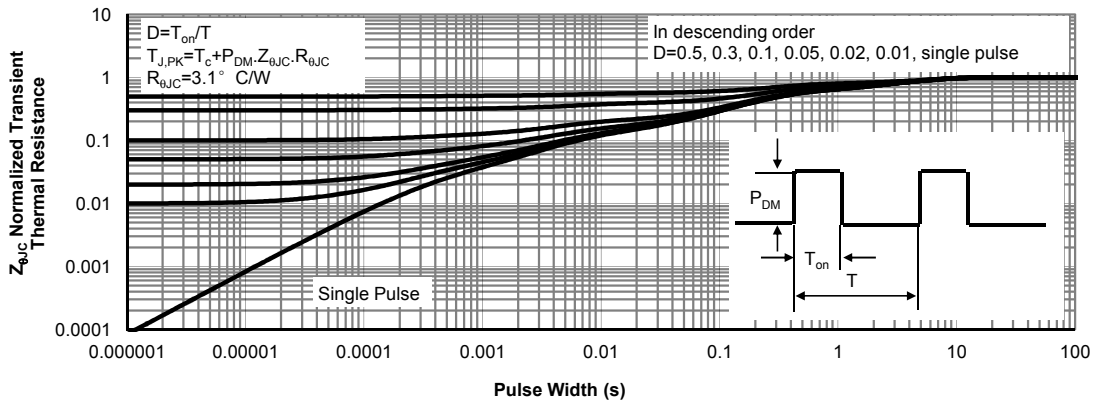
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



**Figure 13: Normalized Maximum Transient Thermal Impedance for AOT(B)12N65 (Note F)**

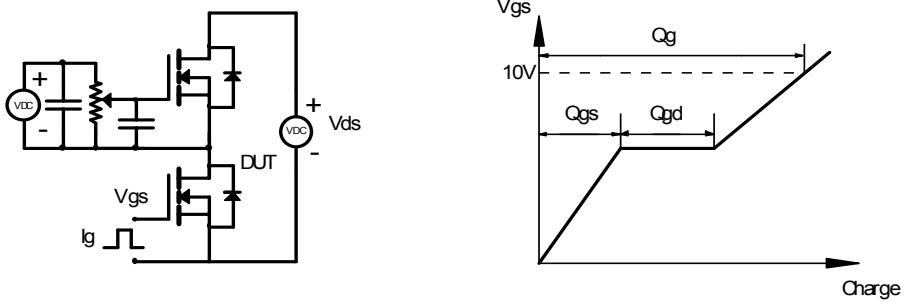


**Figure 14: Normalized Maximum Transient Thermal Impedance for AOTF12N65 (Note F)**

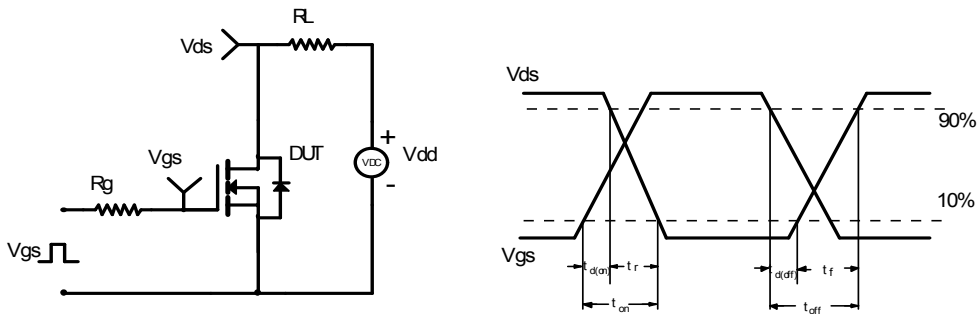


**Figure 15: Normalized Maximum Transient Thermal Impedance for AOTF12N65L (Note F)**

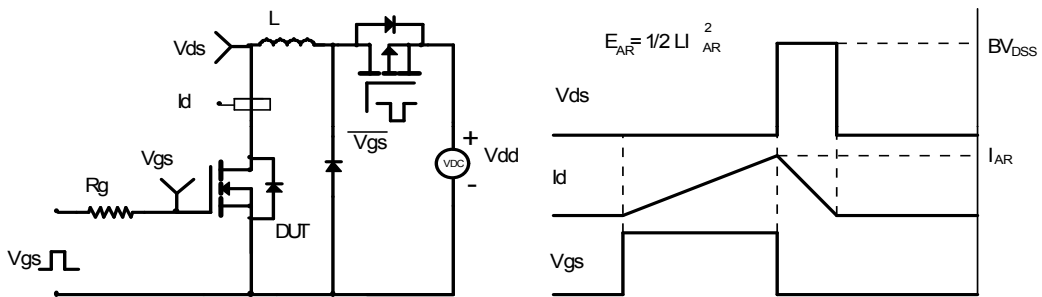
Gate Charge Test Circuit & Waveform



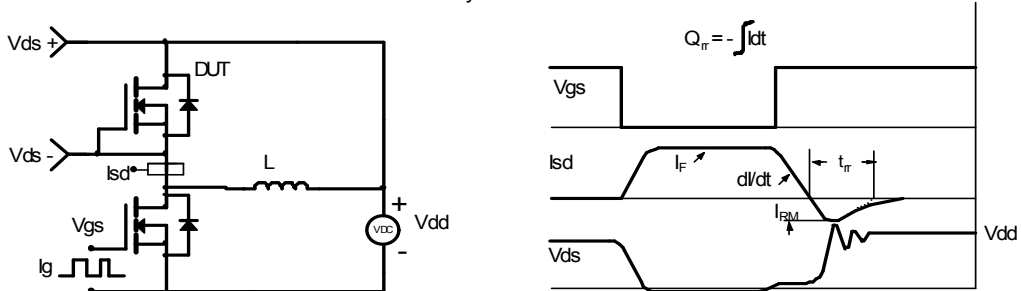
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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